



ShenZhen LuGuang Electronic Technology. Co., Ltd.

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Email:sales05@lgesemi.com Web: www.lgesemi.com

Tel: 0086-755-23981105 Fax: 0086-755-23981125

Mobile/WhatsApp:+86-18676792337 Skype ID: jokucn

10N65

650V N-Channel MOSFET.

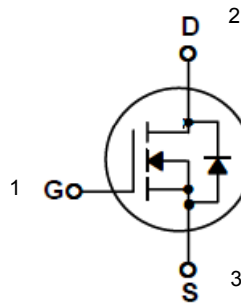
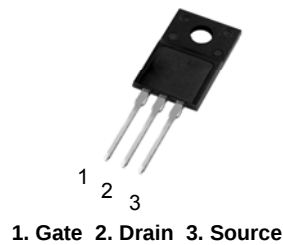
Features

- 10A, 650V, $R_{DS(on)}=0.63\Omega$ @ $V_{GS}=10$ V
- Low gate charge (typical 45 nC)
- Low Crss (typical 12pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

General Description

This Power MOSFET is produced by HSDQ using its own advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

TO-220F Package



Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	650	V
I_D	Drain Current - Continuous ($T_C=25^\circ\text{C}$) - Continuous ($T_C=100^\circ\text{C}$)	10	A
		6.3*	A
I_{DM}	Drain Current - Pulsed (Note 1)	40*	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	606	mJ
I_{AR}	Avalanche Current (Note 1)	10	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	55	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5	V/ns
P_D	Power Dissipation ($T_C=25^\circ\text{C}$) - Derate above 25°C	27.5	W
		0.22	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.54	$^\circ\text{C/W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	42.2	$^\circ\text{C/W}$

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	650			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D=250\text{ }\mu\text{A}$, Referenced to 25°C		0.64		V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$			1	μA
		$V_{DS}=520\text{ V}$, $T_C=125^\circ\text{C}$			10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS}=30\text{ V}$, $V_{DS}=0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS}=-30\text{ V}$, $V_{DS}=0\text{ V}$			-100	nA
On Characteristics						
$V_{GS(TH)}$	Gate Threshold voltage	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$	2.0		4.0	V
$R_{DS(On)}$	Drain-Source on-state resistance	$V_{GS}=10\text{ V}$, $I_D=5\text{ A}$, $T_J=25^\circ\text{C}$		0.63	0.81	Ω
g_{FS}	Forward Transconductance	$V_{DS}=40\text{ V}$, $I_D=5\text{ A}$ (Note 4)		10.5		S
Dynamic Characteristics						
C_{iss}	Input capacitance	$V_{DS}=25\text{ V}$, $V_{GS}=0\text{ V}$, $f=1.0\text{ MHz}$		1998		pF
C_{oss}	Output capacitance			174		pF
C_{rss}	Reverse transfer capacitance			12		pF
Switching Characteristics						
$t_{d(on)}$	Turn On Delay Time	$V_{DD}=325\text{ V}$, $I_D=10\text{ A}$, $R_G=25\text{ }\Omega$ (Note 4, 5)		24		ns
t_r	Rising Time			37		ns
$t_{d(off)}$	Turn Off Delay Time			114		ns
t_f	Fall Time			43		ns
Q_g	Total Gate Charge	$V_{DS}=520\text{ V}$, $I_D=10\text{ A}$, $V_{GS}=10\text{ V}$ (Note 4, 5)		45		nC
Q_{gs}	Gate-Source Charge			11		nC
Q_{gd}	Gate-Drain Charge			17		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current				10	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current				40	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0\text{ V}$, $I_S=10\text{ A}$			1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0\text{ V}$, $I_S=10\text{ A}$, $di_F / dt=100\text{ A}/\mu\text{s}$ (Note 4)		520		ns
Q_{rr}	Reverse Recovery Charge			4.3		μC
Notes:						
1. Repetitive Rating : Pulse width limited by maximum junction temperature						
2. $L=12.1\text{ mH}$, $I_{AS}=10\text{ A}$, $V_{DD}=50\text{ V}$, $R_G=25\text{ }\Omega$, Starting $T_J=25^\circ\text{C}$						
3. $I_{SD}\leq 10\text{ A}$, $di/dt\leq 200\text{ A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$						
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$						
5. Essentially independent of operating temperature						

Typical Characteristics

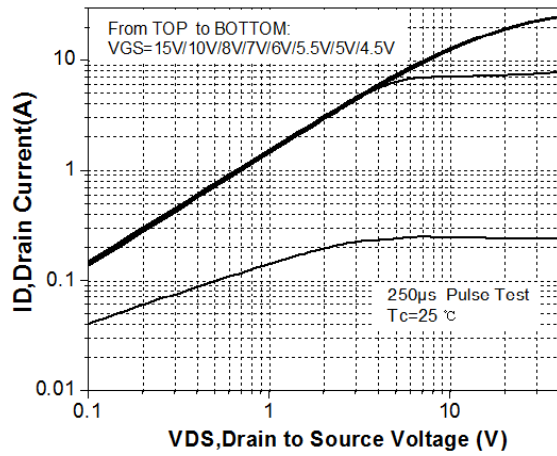


Figure 1. On-Region Characteristics

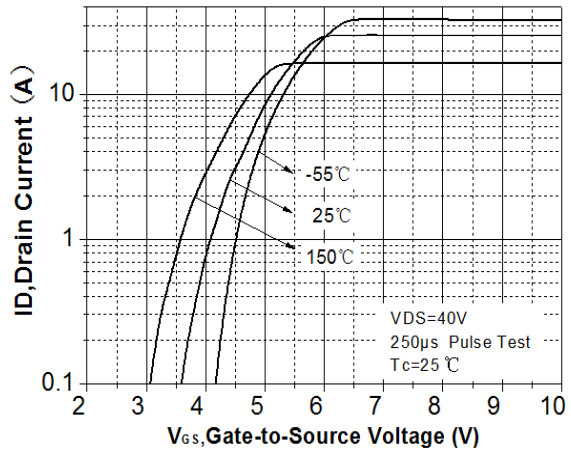


Figure 2. Transfer Characteristics

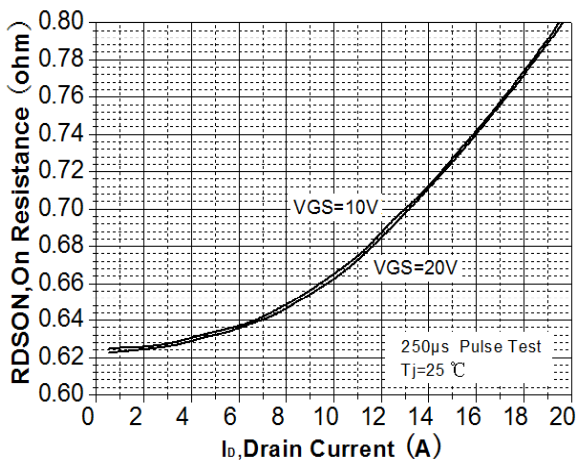


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

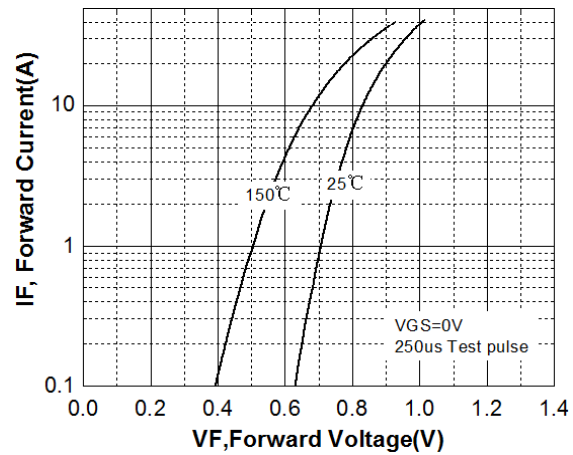


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

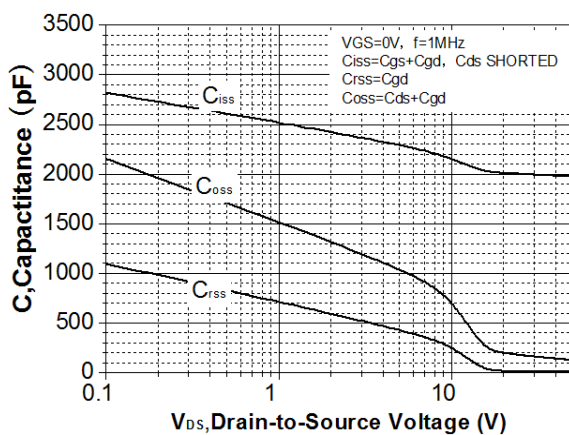


Figure 5. Capacitance Characteristics

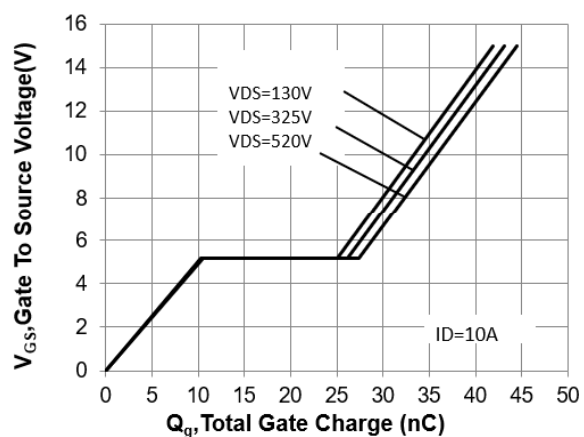


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

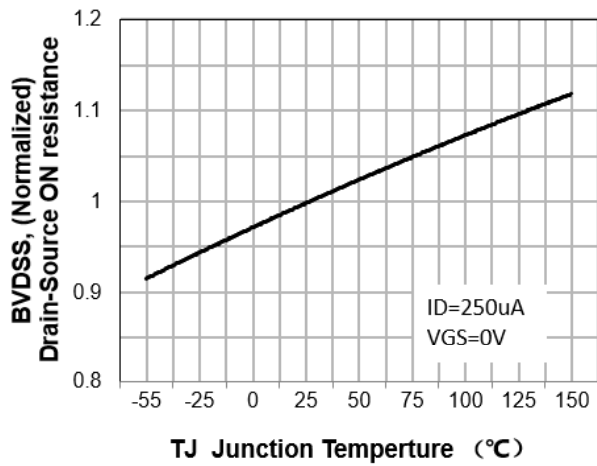


Figure 7. Breakdown Voltage Variation vs Temperature

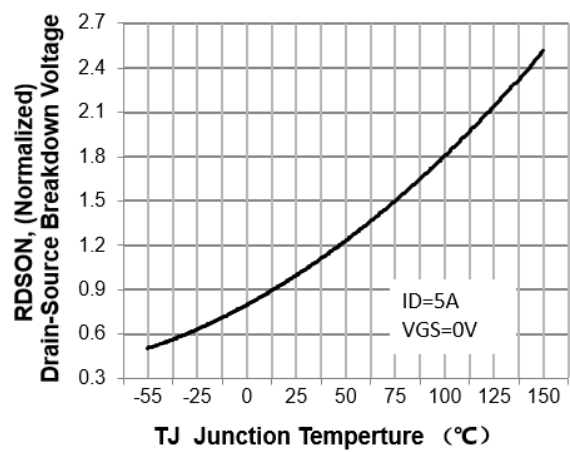


Figure 8. On-Resistance Variation vs Temperature

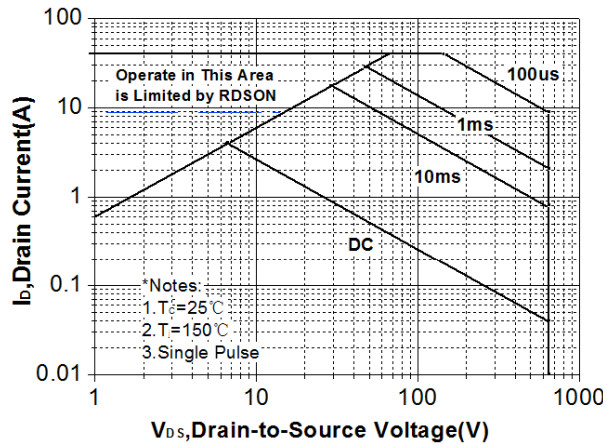


Figure 9. Maximum Safe Operating Area

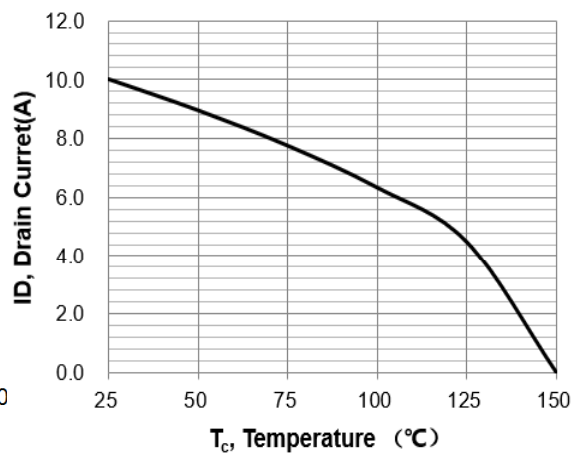


Figure 10. Maximum Drain Current vs Case Temperature

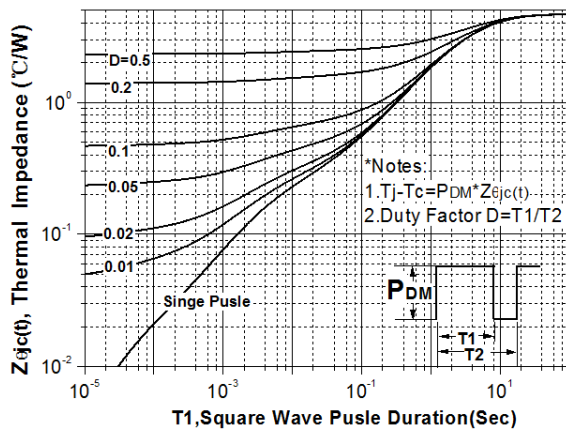
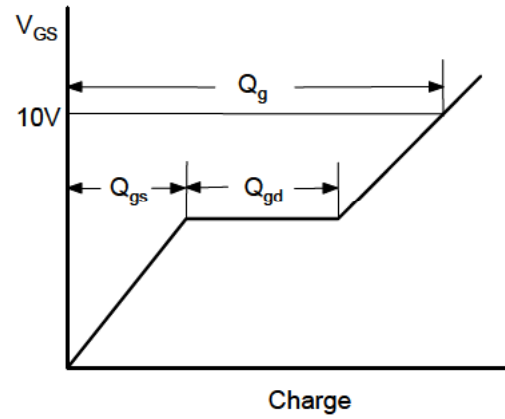
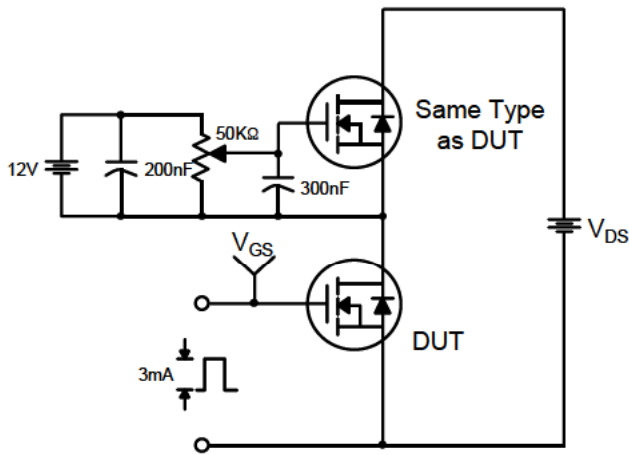
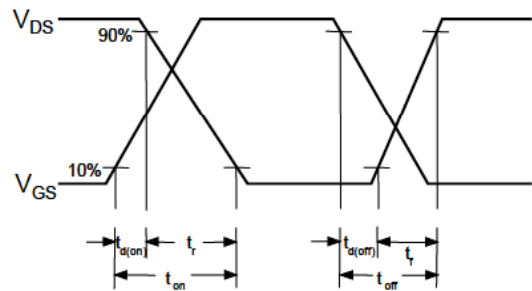
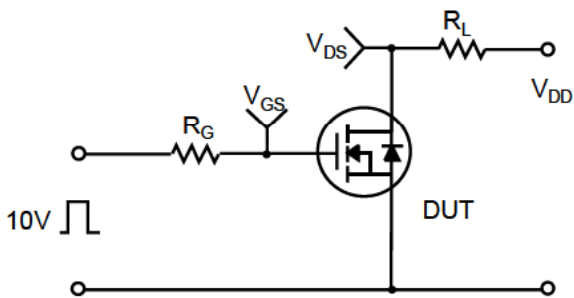


Figure 11. Transient Thermal Response Curve

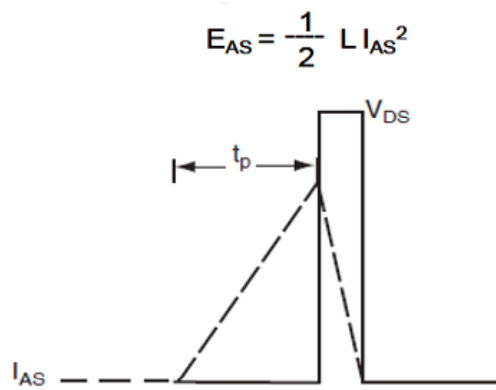
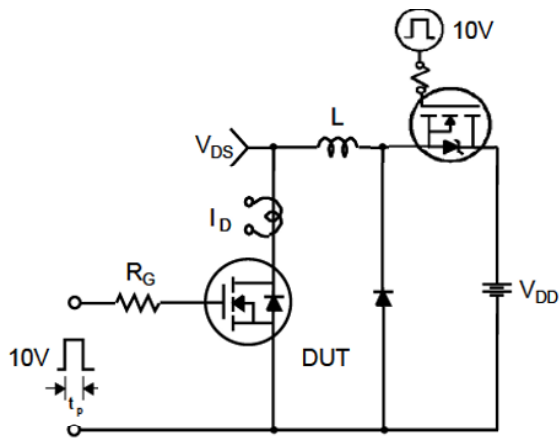
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

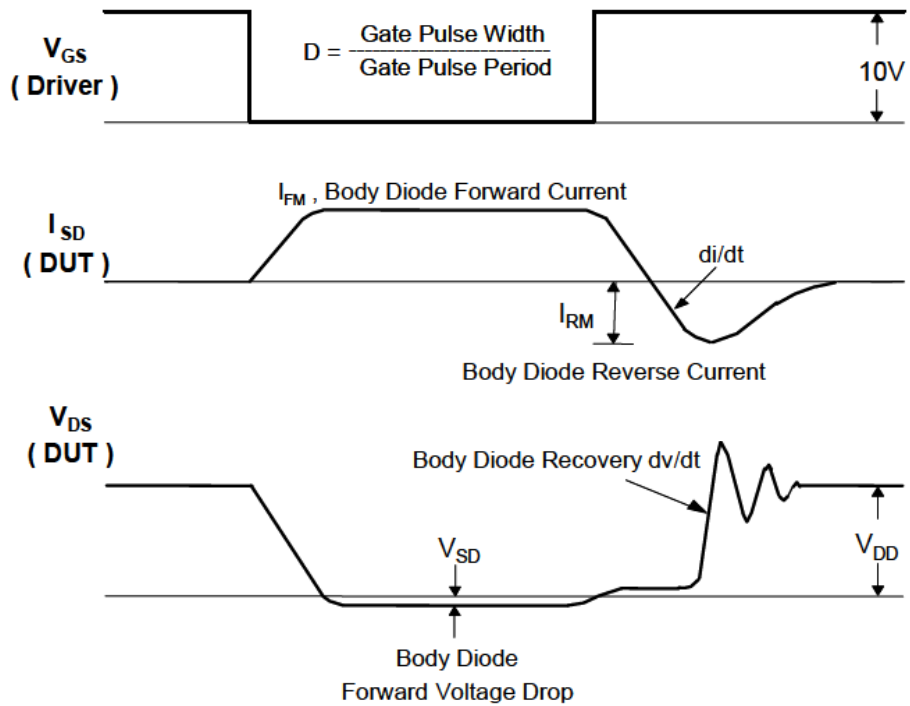
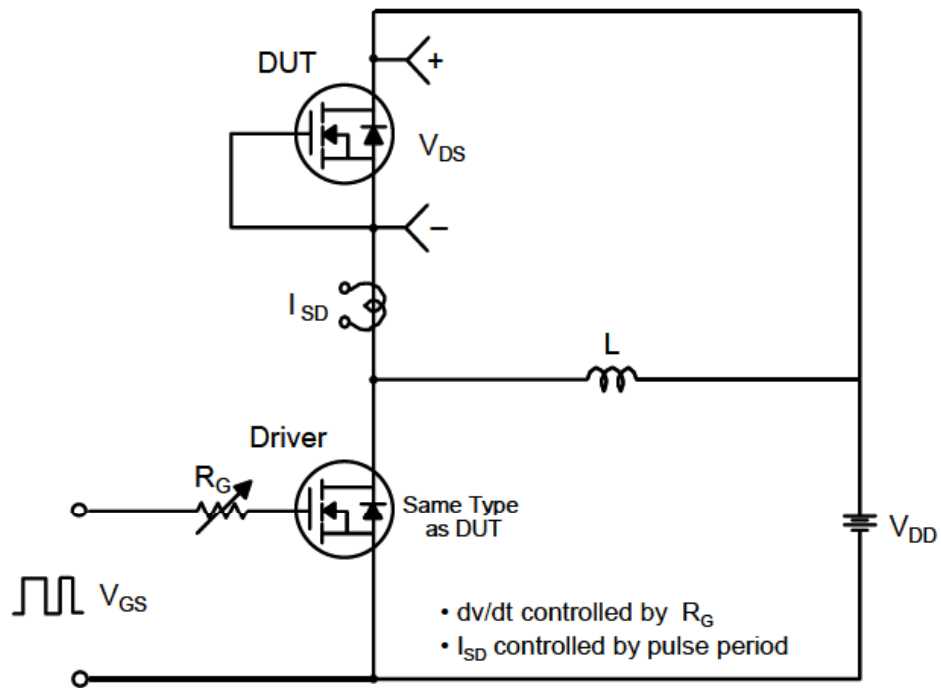


Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2$$

Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO220F

